

Can dreatly absorb a photon with energy Eph = Ey snoe sk = 0 alrealy. 6) Indrect Bendgap I En com phonon UB Indrect grap : prest mmmm m conductory band days not live dreetly above highest more mun in valence band. Hence ; induct bandpup semiconductors do not dreatly absorb a photon with energy Epn = Ey sure a phonon with approprishe k : reeded as well (and phonons follow a statistical defibution of ereques (momenta). II) Direct is Indirect Bondors P Exercise Consider two materials, semiconductor A and Semiconductor B. A has a direct bordgrap while B has an indirect badgop. a) Whitch material has a larger absorption

a) Which making has a larger absorption coefficient of? You can assume the incident light is above bendgrap for both. b) Suppose you wont to make a solar all. Both materials are assiluble, but only in one thickness t = 525 um. Which would you use if you want to extract as much every from the light as passible? How would you improve the alsorption د) of an induct bundgesp material in general? d) It turns out that Silicon is an indirect bandges p material, white other options like Grats are direct. Why is Si the man solar parel marterial than? GraAs Absorption Spectrum Ш $\times 10^{4}$ 1.1 cm⁻¹ 0.9 \$0K. 186 K 0.7 294 K 1.54 1.48 150 1.52 144 1.46 e₩ 142

(i) Let's look at the room T (294K) absorption spectrum First, Agam, Grafts is a direct gop semiconductor. How would you expect the plat to Change if Galts was inderect? 6) The spectrum clearly charges as the tenperature changes, Do the changes make sense? C) What do you that those peaks of low temperature one?